



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92S Plastic-Encapsulate Transistors

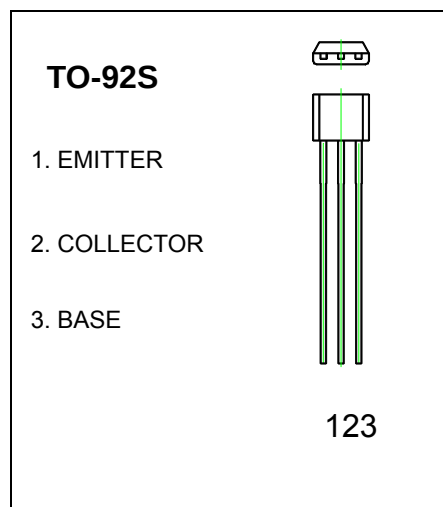
KTC3195 TRANSISTOR (NPN)

FEATURES

- Small reverse transfer capacitance $C_{re}=0.7\text{pF(Typ)}$
- Low noise Figure: $NF=2.5\text{dB(Typ.)}$

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	20	mA
P_C	Collector Power Dissipation	400	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	40		200	
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=1\text{mA}$	300	550		MHz
Reverse Transfer capacitance	C_{re}	$V_{CB}=6\text{V}, I_E=0, f=1\text{MHz}$		0.7		pF
Noise figure	NF	$V_{CE}=6\text{V}, I_C=1\text{mA}, f=100\text{MHz}$		2.5	5	dB
Power Gain	G_{pe}			18		dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	40-80	70-140	100-200
Marking			

Typical Characteristics

KTC3195

